AN1228: FET Selection Guide for Si347x PSE Families

The Si347x family of Power over Ethernet PSE devices, including the Si3471 and Si3474, utilizes external FETs to improve thermals.

To meet the strict timing requirements demanded by the IEEE 802.3af, 802.3at, and 802.3bt standards, external FETs must meet certain requirements. This application note details the key parameters needed when selecting an external FET and lists the FETs Silicon Labs has tested with the Si347x family of devices.

For more information on choosing a FET or to review a specific FET, please contact us at www.silabs.com/support.

KEY TOPICS

- Compatible FETs
- Important FET parameters
- Safety considerations

1. FET Parameters and Tested FETs

The table below summarizes the key FET parameters and the target value for compatibility with the Si347x families. It lists the FETs Silicon Labs has tested to be compatible with the Si347x families. Please refer to the data sheets of each FET for the latest specifications.

Drain-source resistanc RDS(ON) is a key parameter to ensure thermal performance, particularly in high port count designs. Designs using FETs with a high RDS(ON) and a poor layout may experience thermal issues. Please refer to the Si347x EVBs for recommended PCB layout to ensure proper thermal dissipation. In addition, please submit design schematic and layout for a free, confidential review by visiting www.silabs.com/support.

Table 1.1. FETs Tested with the Si347x Families and Key Parameters

Parameter	Total Gate Charge Q_g	Gate-Drain Charge Q_{gd}	Drain-Source Breakdown Voltage $V_{(BR)DSS}$	Drain-Source On-Resistance $R_{DS(ON)}$ at V_{GS} = 10 V	Safe Operating Area
Target	≤ 30 nC	≤ 11 nC	>100 V	<120 mΩ	See Table 1.2
Fairchild FDMC3612	14.4	3.7	100	110	See Figure 1.1
Infineon IRFHM3911	17	5.4	100	115	See Figure 1.2
Nexperia PSMN075	16.4	5.2	100	71	See Figure 1.3
Nexperia PSMN040-100MSE	30	10.7	100	36.6	See Figure 1.4
Toshiba SSM6K361NU	3.2	1.5	100	69	See Figure 1.5

All FETs have power limitations (P_FET = V_DS * I_D) above which they will be damaged after a certain amount of time. The Safe-Operating-Area (SOA) curve represents the V_DS/I_D limitations for a given FET. The IEEE 802.3bt standard specifies the amount of time a PD is allowed to draw current above its assigned class. Care must be taken to select a FET with an SOA curve that can withstand the Si347x's implementation of the IEEE 802.3bt standard. These parameters are listed in the table below. The Si347x family of PSEs are always Type 3 or Type 4 and follow the current limit based on PD class.

Table 1.2. Si347x Overcurrent Time and Current Limiting Per Pair Set

PD Class	Si347x Maximum Overcurrent Time	Si347x Current Limit Per Pair Set	Drain to Source Voltage	SOA Curve Point
0, 1, 2, 3	15 ms	425 mA	30 V	Point 1
4, 5, 6, 7, 8	9 ms	1275 mA	15 V	Point 2

The following figure shows an example SOA curve with the IEEE Type 1, 2, 3, and 4 limits identified. Note that Type 1 is marginal using this FET.

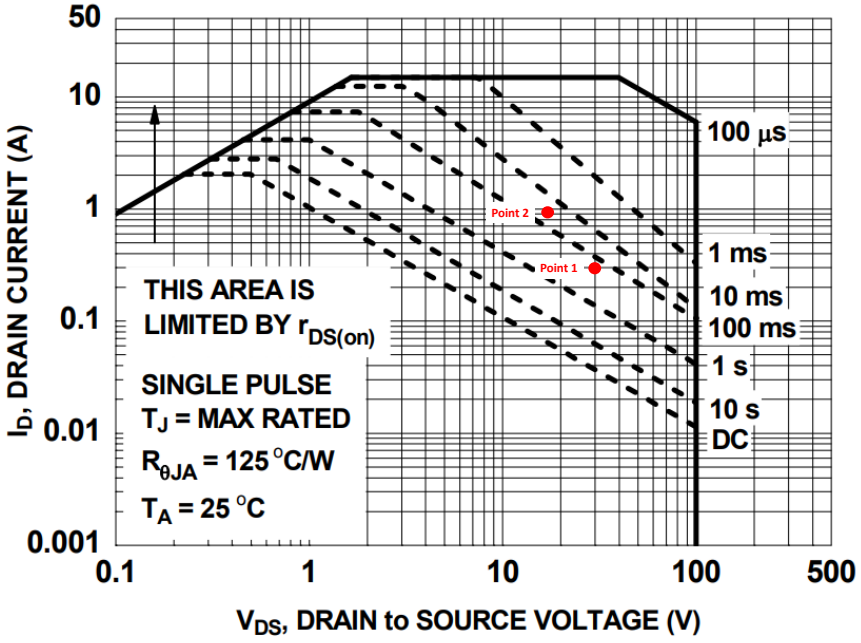


Figure 1.1. FDMC3612 FET SOA Curves with Worst-Case Points Highlighted

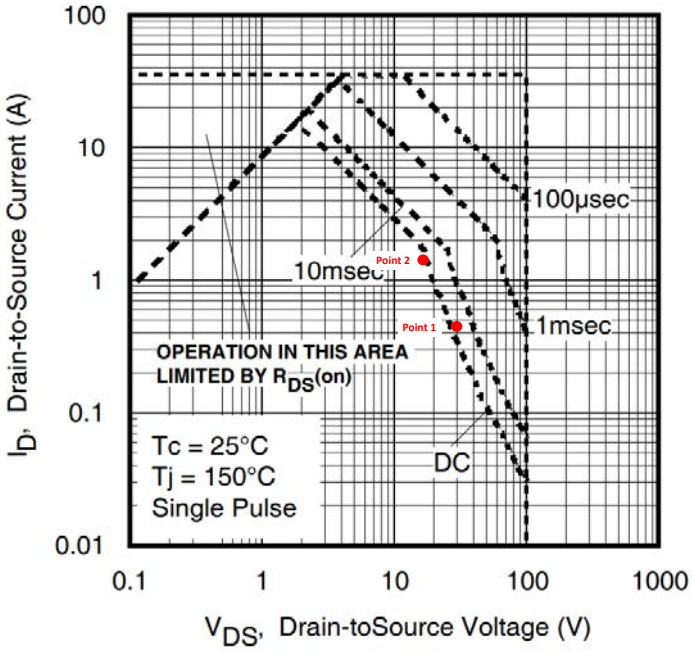


Figure 1.2. IRFHM3911PbF FET SOA Curves with Worst-Case Points Highlighted

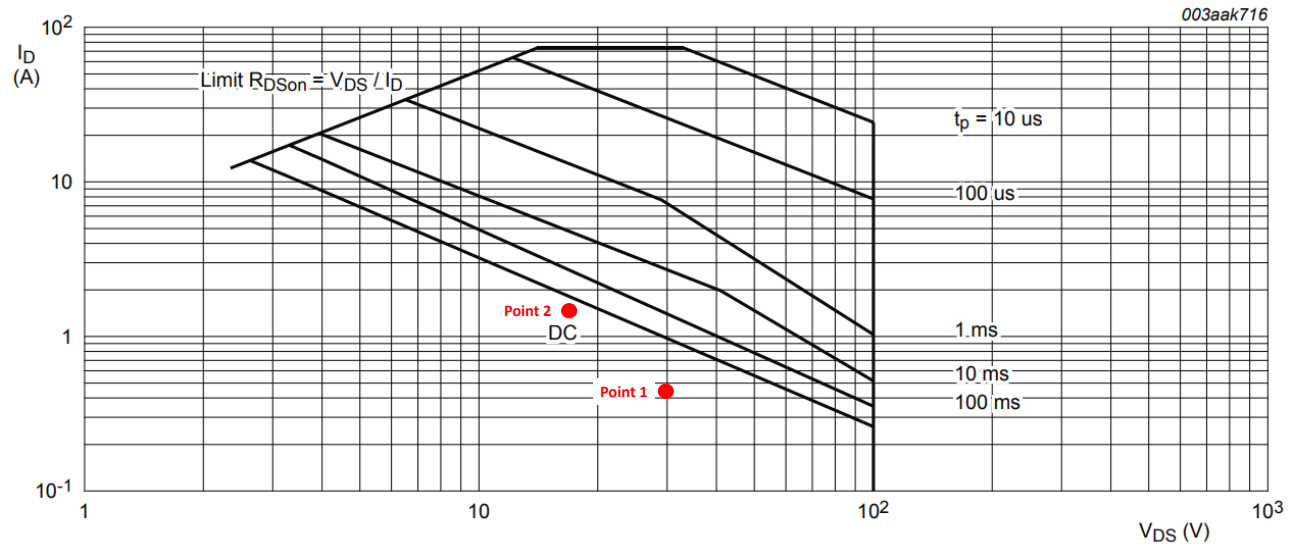


Figure 1.3. PSMN075-100MSE FET SOA Curves with Worst-Case Points Highlighted

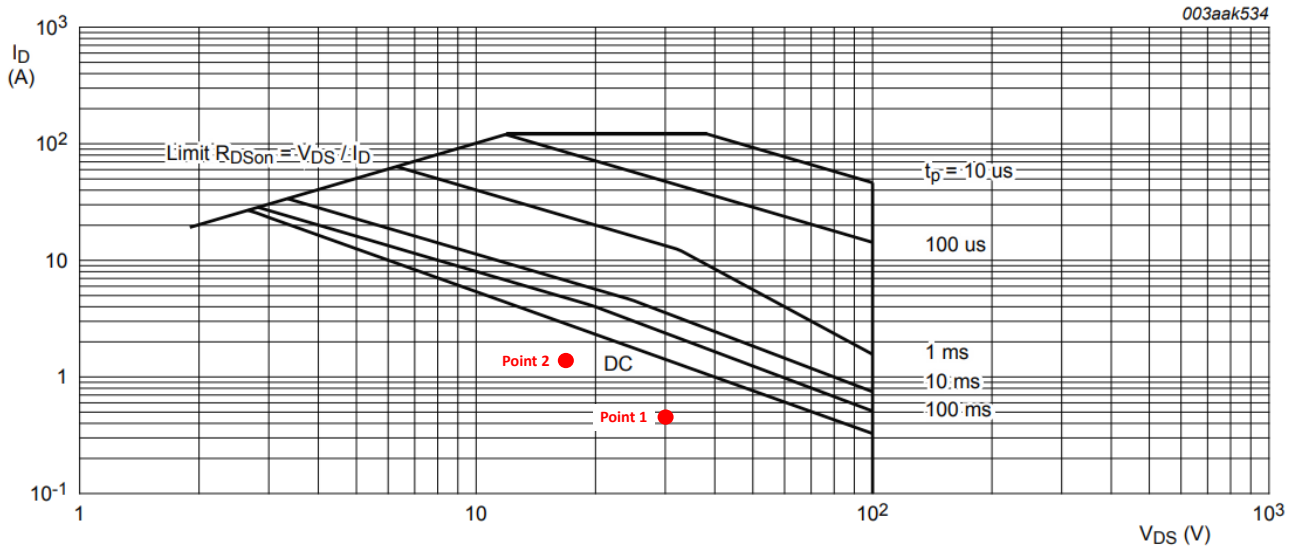


Figure 1.4. PSMN040-100MSE FET SOA Curves with Worst-Case Points Highlighted

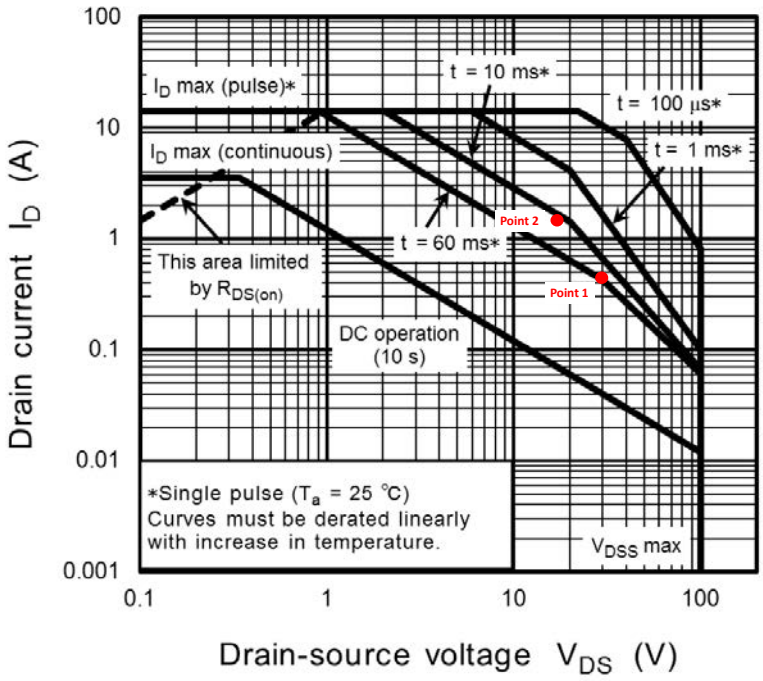
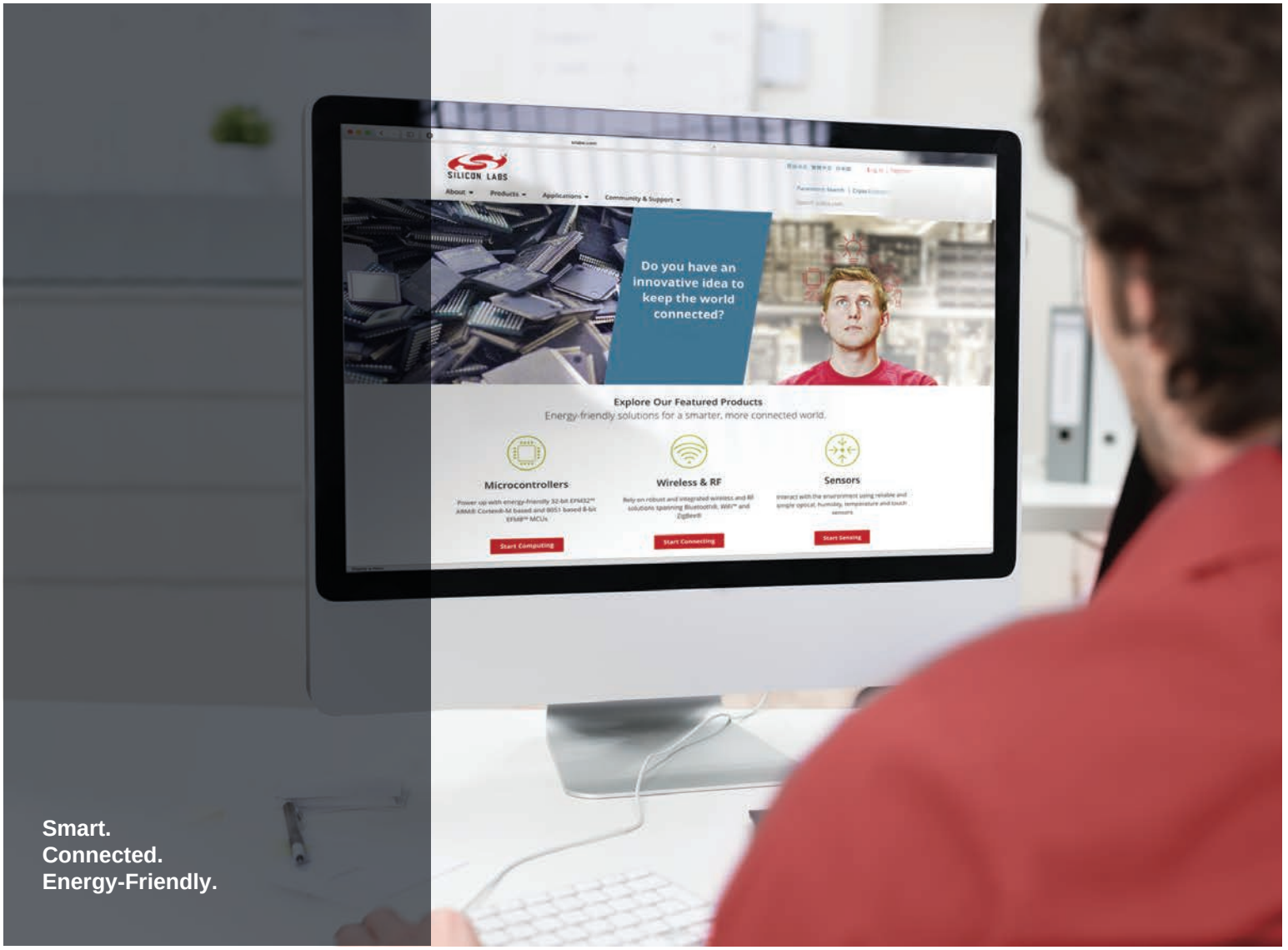


Figure 1.5. SSM6K361NU FET SOA Curves with Worst-Case Points Highlighted



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